

SEMiX101GD126HDs



Trench IGBT Modules

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Features

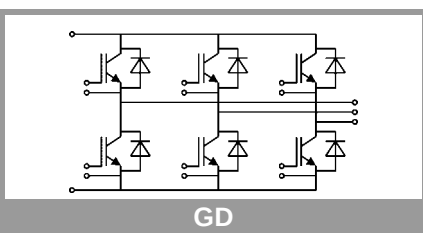
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design



Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1200	V
I _C	T _j = 150 °C	T _c = 25 °C	129	A
		T _c = 80 °C	91	A
I _{Cnom}			75	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		150	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 600 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 125 °C	10	μs
T _j			-40 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	117	A
		T _c = 80 °C	81	A
I _{Fnom}			75	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		150	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		600	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}			600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 75 A	T _j = 25 °C		1.7	2.1	V
	V _{GE} = 15 V chipelevel	T _j = 125 °C		2	2.45	V
V _{CE0}		T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}		T _j = 25 °C		9.3	12.0	mΩ
	V _{GE} = 15 V	T _j = 125 °C		14.7	18.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 3 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.1	0.3	mA
	V _{CE} = 1200 V	T _j = 125 °C				mA
C _{ies}		f = 1 MHz		5.3		nF
C _{oes}	V _{CE} = 25 V	f = 1 MHz		0.28		nF
C _{res}	V _{GE} = 0 V	f = 1 MHz		0.24		nF
Q _G	V _{GE} = - 8 V...+ 15 V			600		nC
R _{Gint}	T _j = 25 °C			10.00		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C		225		ns
t _r	I _C = 75 A	T _j = 125 °C		40		ns
E _{on}		T _j = 125 °C		10		mJ
t _{d(off)}	R _{G on} = 2 Ω	T _j = 125 °C		470		ns
	R _{G off} = 2 Ω	T _j = 125 °C		85		ns
t _f		T _j = 125 °C		85		ns
E _{off}		T _j = 125 °C		11		mJ
R _{th(j-c)}	per IGBT				0.27	K/W

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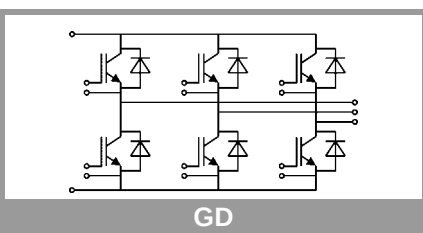
Typical Applications*

- AC inverter drives
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 75 A V _{GE} = 0 V chip	T _j = 25 °C		1.6	1.80	V
		T _j = 125 °C		1.6	1.8	V
V _{F0}		T _j = 25 °C	0.9	1	1.1	V
		T _j = 125 °C	0.7	0.8	0.9	V
r _F		T _j = 25 °C	6.7	8.0	9.3	mΩ
		T _j = 125 °C	9.3	10.7	12.0	mΩ
I _{RRM}	I _F = 75 A di/dt _{off} = 2240 A/μs V _{GE} = -15 V V _{CC} = 600 V	T _j = 125 °C	97			A
Q _{rr}		T _j = 125 °C	20			μC
E _{rr}		T _j = 125 °C	9			mJ
R _{th(j-c)}		per diode				0.46
Module						
L _{CE}			20			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.04			K/W
M _s	to heat sink (M5)		3	5		Nm
M _t		to terminals (M6)	2.5	5		Nm
					Nm	
w			350			g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



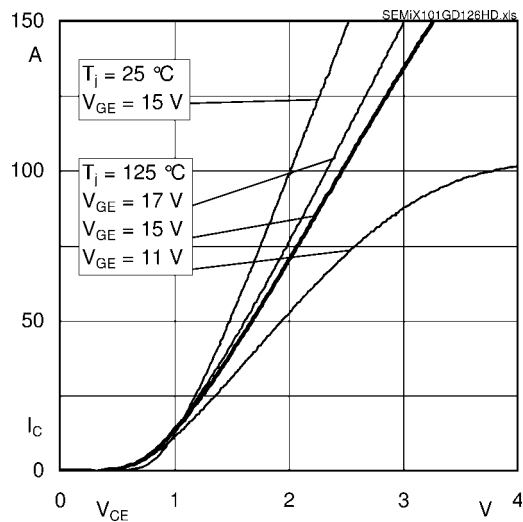


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

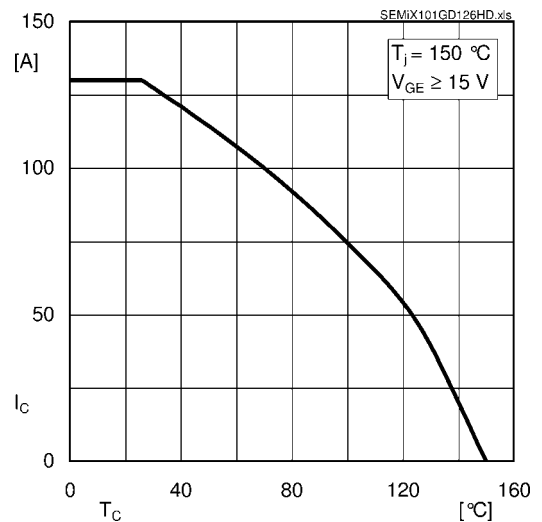


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

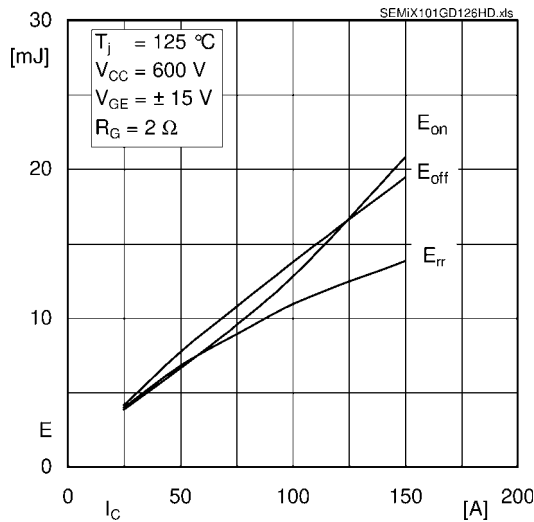


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

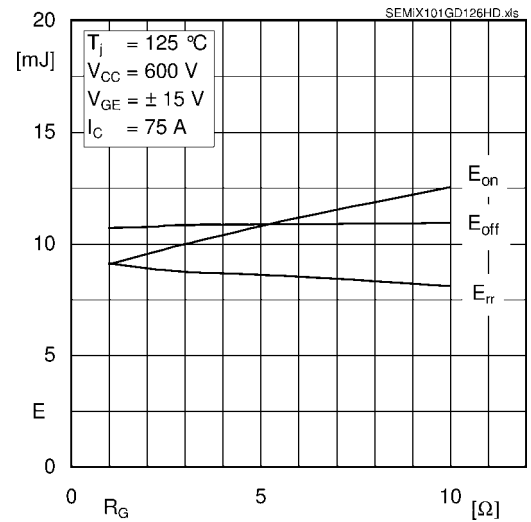


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

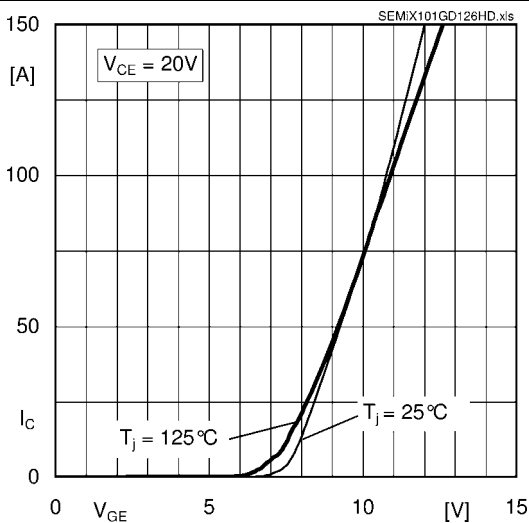


Fig. 5: Typ. transfer characteristic

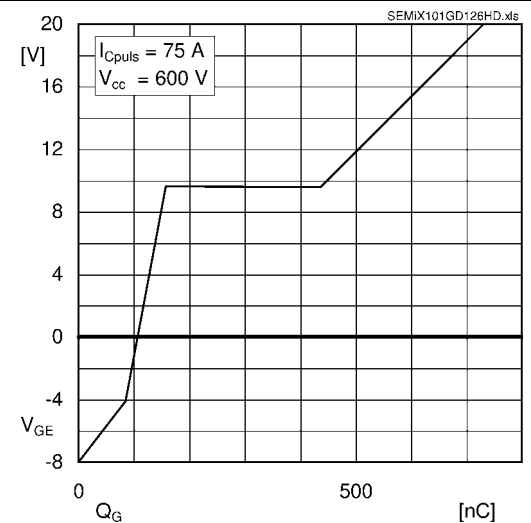
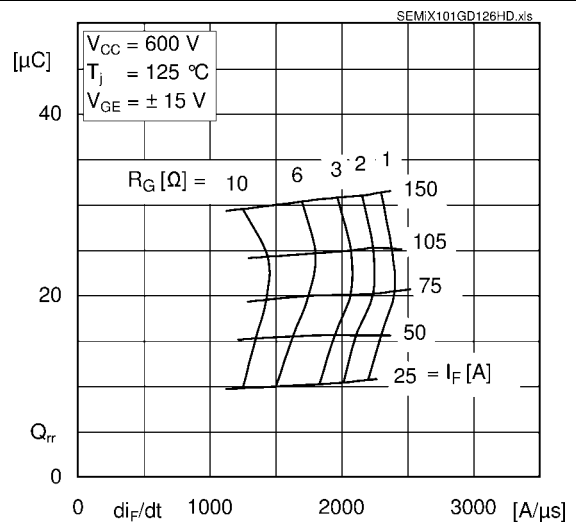
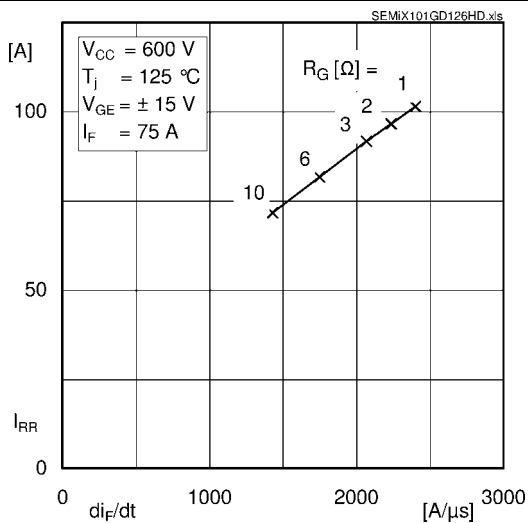
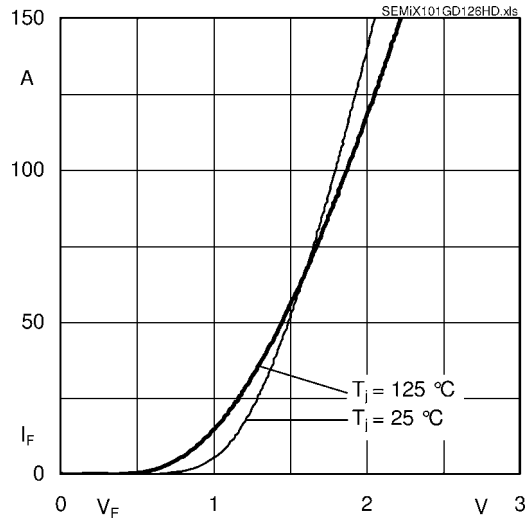
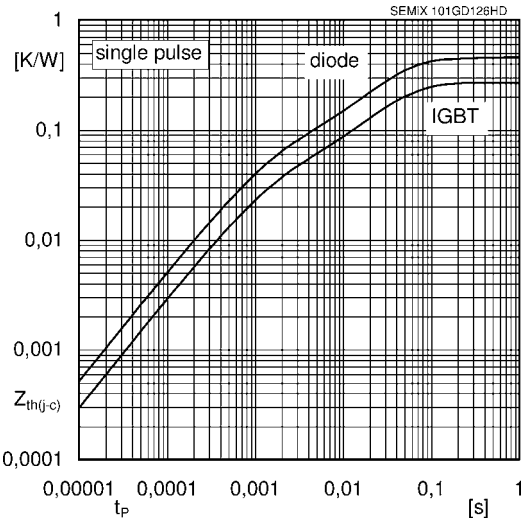
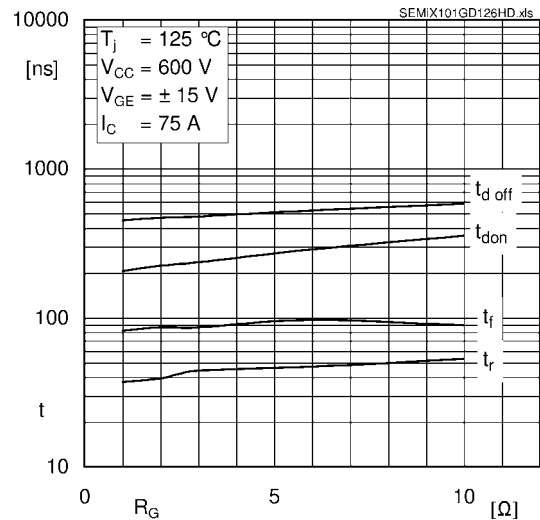
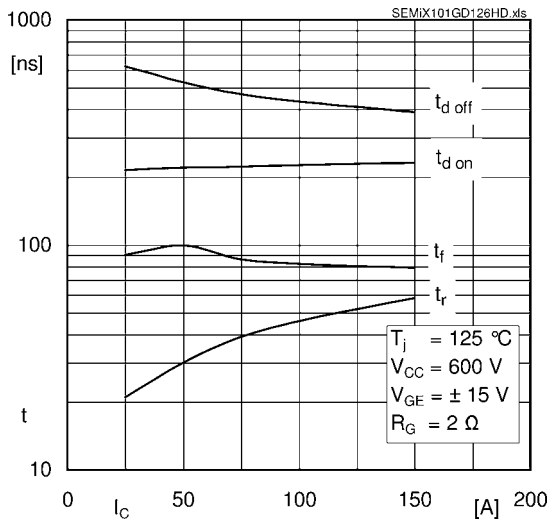
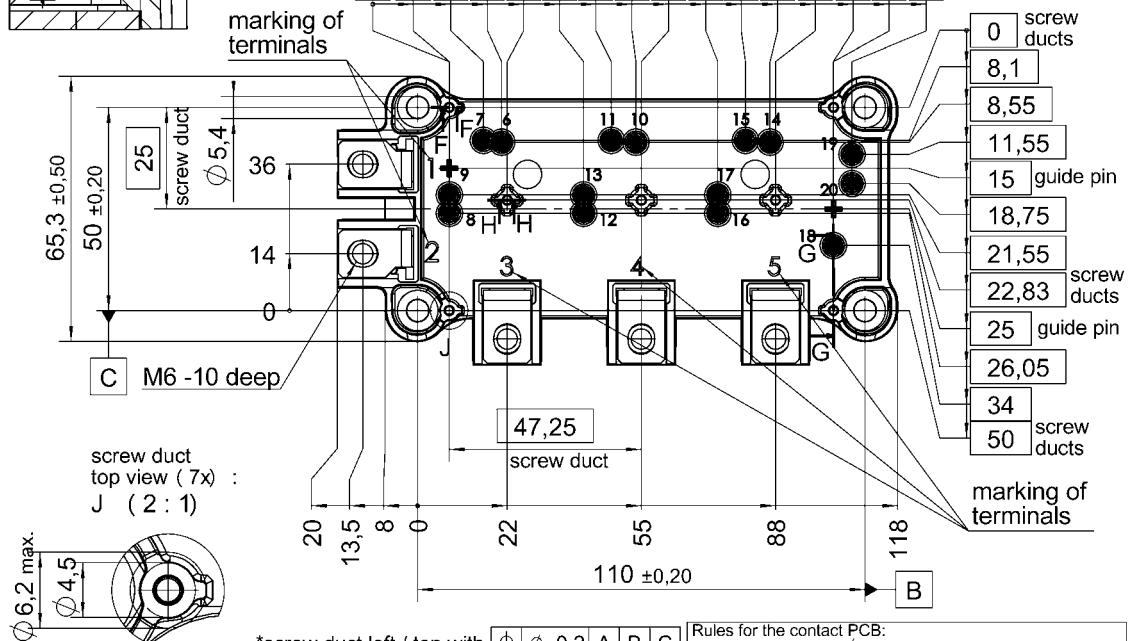
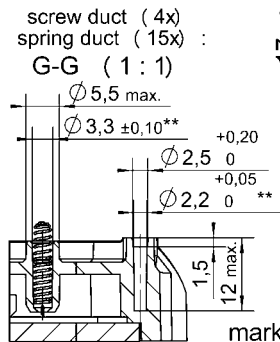
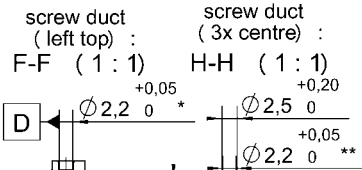


Fig. 6: Typ. gate charge characteristic



Case: SEMiX 13



*screw duct left / top with $\phi 0.2$ A B C

**screw ducts / guide pins / spring ducts with $\phi 0.2$ A D C

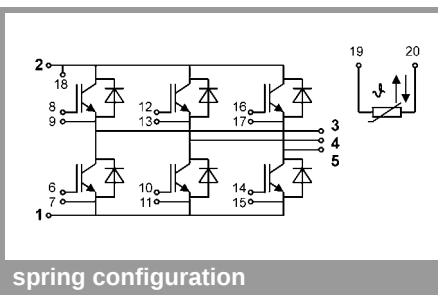
Rules for the contact PCB:

- holes guidepins = $\phi 4 \pm 0.1$ / position tolerance ± 0.1
- holes for screws = $\phi 2.9 \pm 0.1$ / position tolerance ± 0.1
- spring contact pad = $\phi 3.6 \pm 0.1$ / position tolerance ± 0.1

general tolerance:
ISO 2768-mK
ISO 8015

All measures in Z-direction
valid when mounted to heat sink

SEMiX 13



spring configuration

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.